DIALOG(R)File 352:Derwent WPI
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009135736 **Image available**
WPI Acc No: 1992-263174/199232
XRAM Acc No: C92-117379
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Thin-film semiconductor circuit prodn. for display panel - includes forming circuit on film-covered substrate bonding second substrate to circuit-formed face and etching covering film NoAbstract
Patent Assignee: NIPPON TELEGRAPH & TELEPHONE CORP (NITE)
Number of Countries: 001 Number of Patents: 001
Patent Family:

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Title Terms: THIN; FILM; SEMICONDUCTOR; CIRCUIT; PRODUCE; DISPLAY; PANEL; FORMING; CIRCUIT; FILM; COVER; SUBSTRATE; BOND; SECOND; SUBSTRATE; CIRCUIT; FORMING; FACE; ETCH; COVER; FILM; NOABSTRACT
Derwent Class: L03; P81; U14
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FORMATION OF SEMICONDUCTOR CIRCUIT

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ABSTRACT

PURPOSE: To allow the transfer of circuits without using a costly polishing device by sticking a 1st substrate which is formed of the circuits with a 1st film or the 1st film and at least one layer of a 2nd film to a 2nd substrate on the side where the above-mentioned circuits are formed to each other, then etching away the 1st film and transferring the circuits onto the 2nd substrate.

CONSTITUTION: A molybdenum film is first deposited at the 1st film 12 on the 1st substrate 11 consisting of Si. An SiO(sub 2) film is then deposited as the 2nd film 13 thereon and thereafter, TFTs 17 formed by using a-Si as well as picture element electrodes 18 consisting of ITO (indium tin oxide) and wirings consisting of A1 are formed thereon to produce an active matrix 14. An adhesive 15 of, for example, an epoxy system is then applied on the matrix 14 and a PET film is stuck as the 2nd substrate 16 onto the circuits. The assembly is thereafter immersed into hydrogen peroxide and the molybdenum film 12 is completely removed by etching. Finally, the 1st substrate 11 is completely peeled and the above-mentioned circuits are completed.